

**BYC30MW-650PT2** 

Hyperfast power diode

Rev.03 - 22 May 2023

**Product data sheet** 

### **1. General description**

Hyperfast power diode in a 2-lead TO247 plastic package.



### 2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

### 3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

### 4. Quick reference data

	uick reference data						
Symbol	Parameter	Conditions	Notes	s Values			Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 109 °C; square-wave pulse		60			A
I <sub>FSM</sub> non-repetitive peak forward current		$t_{p}$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u>		270			A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297			А
Symbol	Parameter	Conditions	Notes	Min	Тур	Мах	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 25 °C; Fig. 7		-	20	-	ns
					1		

## **5. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathod	С С С С С С С С С С С С С С С С С С С	

## 6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYC30MW-650PT2		BYC30MW-650PT2Q	Tube	30	TO247L-2L (L)	12-Nov-2020		
					TO247P-2L (P)	31-Mar-2023		

## 7. Marking

Table 4. Marking codes						
Type number	Marking codes					
	Assembly factory: L	Assembly factory: P				
BYC30MW-650PT2	BYC30MW 600PT2 PJLxxxx xx	BYC30MW 600PT2 PJPxxxx xx				

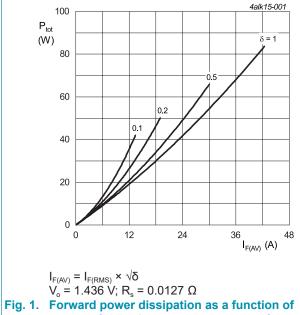
4alk15-002

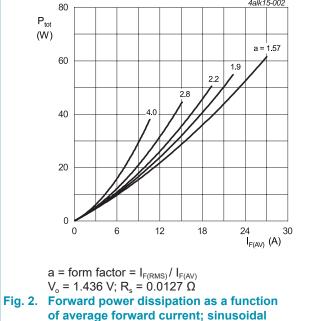
### 8. Limiting values

### Table 5. Limiting values

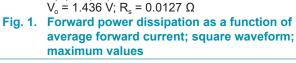
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			650	V
V <sub>RWM</sub>	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 109 °C; square-wave pulse		60	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
Tj	junction temperature			-65 to 175	°C

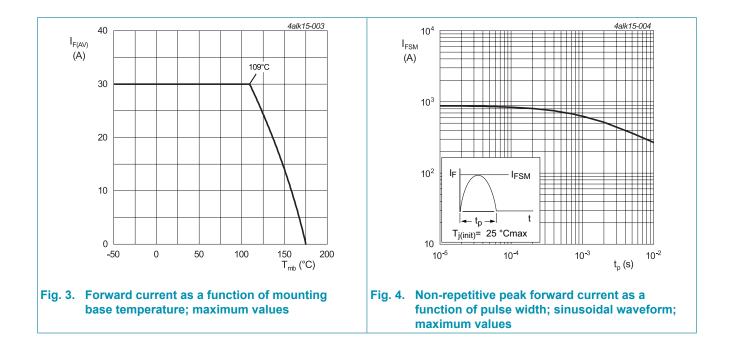




waveform; maximum values

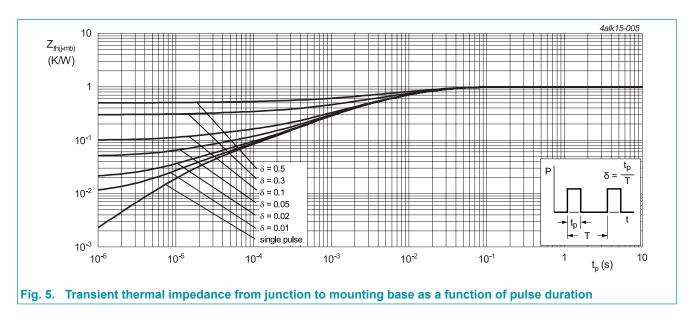


### **BYC30MW-650PT2** Hyperfast power diode



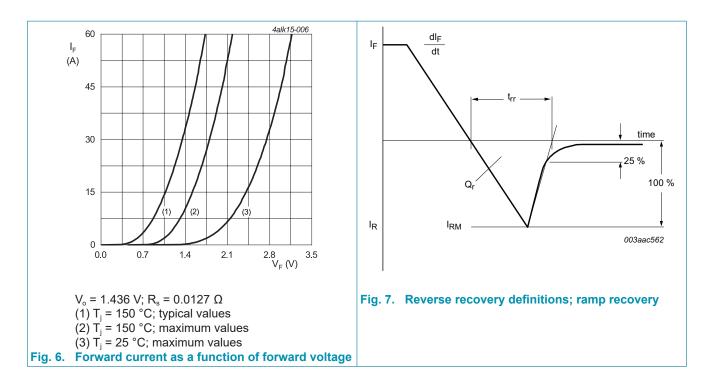
### 9. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	45	-	K/W



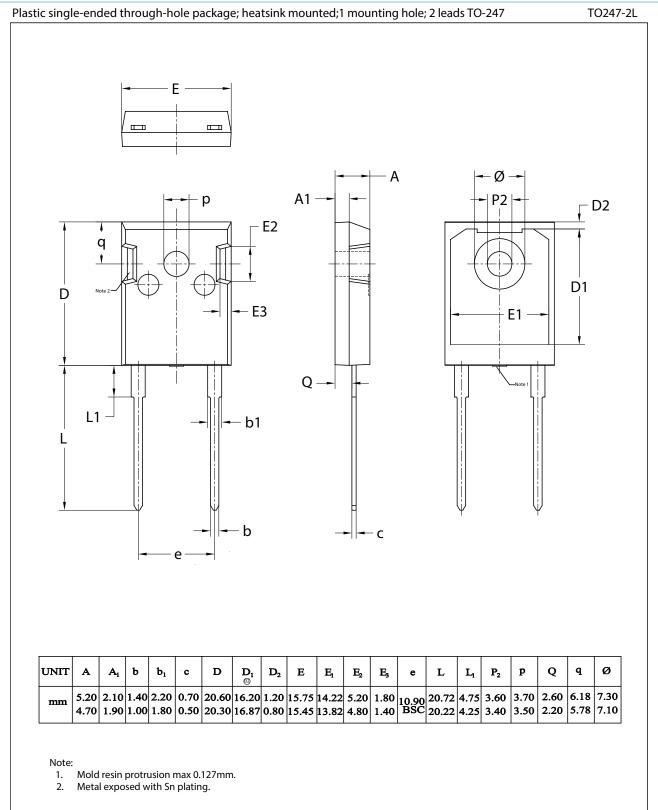
### **10. Characteristics**

	naracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
R	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.6	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.25	1	mA
Dynamic	characteristics	1					
Q <sub>r</sub>	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	68	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	330	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>		-	20	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	38	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	73	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	3.7	-	A
	avalanche energy	I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	9.1	-	A
as	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		30	-	-	mJ

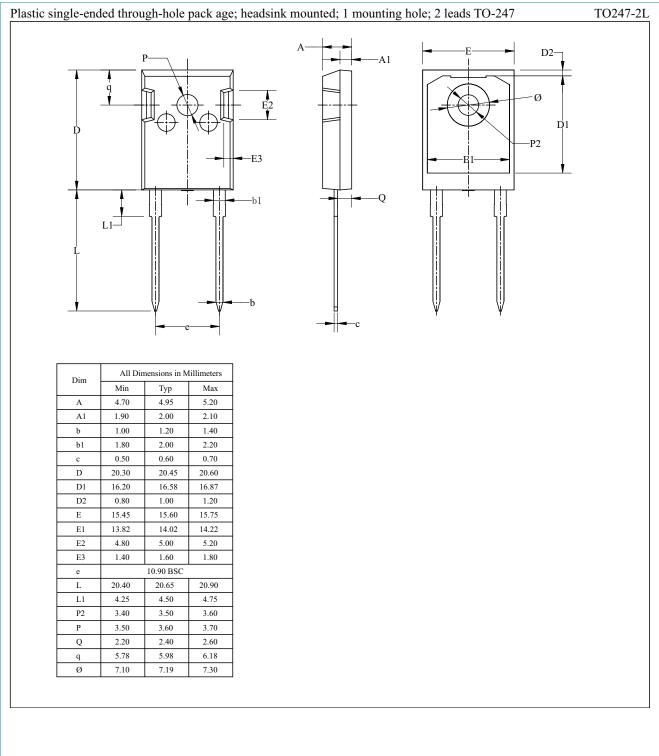


### **11. Package outline**

### Assembly factory: L



### Assembly factory: P



# BYC30MW-650PT2

### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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